

# 2STC5949

# High power NPN epitaxial planar bipolar transistor

### **Features**

- High breakdown voltage V<sub>CEO</sub> = 250 V
- Complementary to 2STA2121
- Typical f<sub>t</sub> = 25 MHz
- Fully characterized at 125 °C

# **Application**

Audio power amplifier

# Description

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor yosolete Productis shows good gain linearity behaviour.

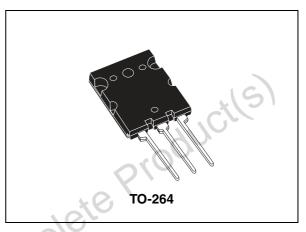
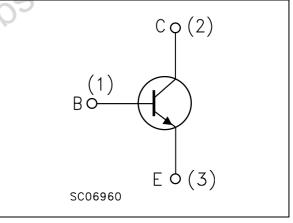


Figure 1. Internal schematic diagram



able 1.	Device	summar
	Device	Summar

Order code	Marking	Package	Packaging
2STC5949	2STC5949	TO-264	Tube

#### Absolute maximum ratings 1

#### Table 2. Absolute maximum rating

V <sub>CEO</sub> V <sub>EBO</sub>	Collector-base voltage ( $I_E = 0$ ) Collector-emitter voltage ( $I_B = 0$ )	250	V
V <sub>EBO</sub>	Collector omittor voltage (L = 0)		
	$Collector-entitien voltage (I_B = 0)$	250	V
۱ <sub>C</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	6	V
	Collector current	17	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	34	А
P <sub>TOT</sub>	Total dissipation at $T_c = 25^{\circ}C$	220	W
T <sub>stg</sub>	Storage temperature	-65 to 150	⊃°C
TJ	Max. operating junction temperature	150	°C
Table 3.	Thermal data	OQV.	

#### Table 3. Thermal data

	Table 0.	mermai data			
	Symbol	Parameter		Value	Unit
	R <sub>thj-case</sub>	Thermal resistance junction-case	max	0.568	°C/W
obsolf			16,	0.568	C/W
0,02					

# 2 Electrical characteristics

(T<sub>case</sub> = 25 °C; unless otherwise specified)

Table 4.	Electrical	characteristics
	LIGOUIDUI	0110100100100

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 250 V			5	μA
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 6 V			5	μA
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50 mA	250		2	V
V <sub>(BR)CBO</sub>	Collector-base breakdown	I <sub>C</sub> = 100 μA	250	と	י ר	V
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA	6			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{\rm C} = 8 \ {\rm A}$ $I_{\rm B} = 800 \ {\rm mA}$			3	V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	$I_{\rm C} = 7  {\rm A}$ $V_{\rm CE} = 5  {\rm V}$			1.5	V
h <sub>FE</sub>	DC current gain		80 35		160	
f <sub>T</sub>	Transition frequency	$I_{\rm C} = 1  \text{A}$ $V_{\rm CE} = 5  \text{V}$		25		MHz

1. Pulsed duration = 300 μs, duty cycle ≤ 1.5%

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## 2.1 Electrical characteristics (curves)

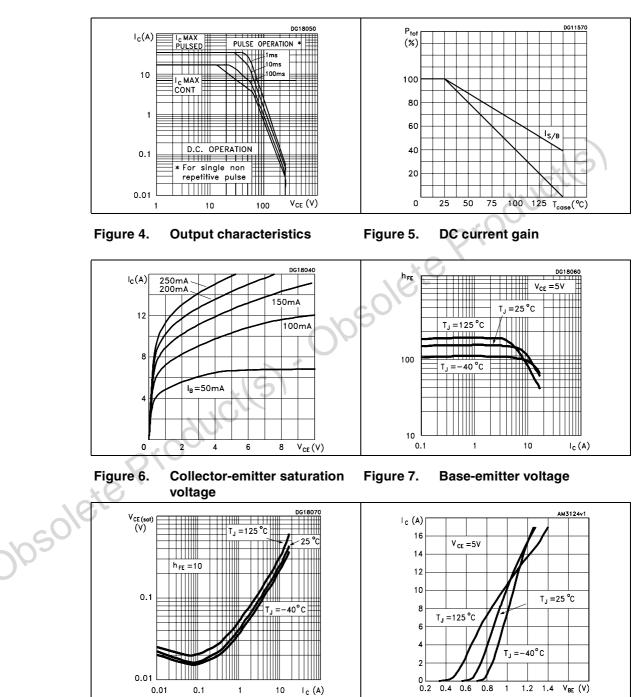


Figure 3.

**Derating curve** 

### Figure 2. Safe operating area

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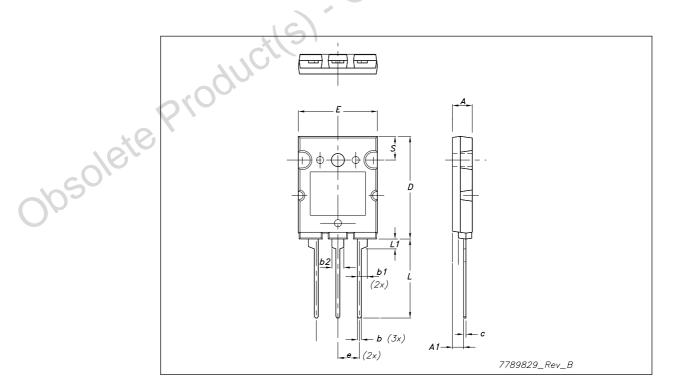
## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s). Obsolete Product(s)

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	TO-264 Mechanical data				
Dim.		mm.			
Dini.	Min.	Тур	Max.		
А	4.80		5.20		
A1	2.50		3.10		
b	0.90	1.0	1.25		
b1		2.5			
b2		2.8			
с	0.50	0.60	0.85		
D	25.6		26.4		
E	19.80	20	20.20		
е	5.15	10,0	5.75		
L	19.50	~O\	20.50		
L1	2.30	3	2.70		
øP	3.55		3.65		



# 4 Revision history

### Table 5. Document revision history

	Date	Revision	Changes
	26-Nov-2007	1	Initial release
	05-May-2008	2	New graphics.
	11-Jul-2008	3	Updated Figure 7.
	17-Nov-2008	4	Content reworked to improve readability, no technical changes
obsole	teprod	ucile	Content reworked to improve readability, no technical changes

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